SILICON DIODE CHIP

This SILICON DIODE CHIP is a Si-based Diode. It has electrical characteristics like lower leakage current, high electrostatic discharge ability and other advantages , it also has extra small size.

Features

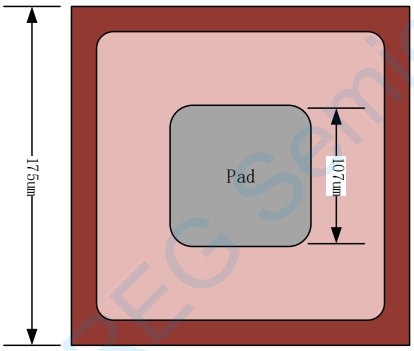
- Si-based NPN type
- Ultra-small size 6.9mil * 6.9mil

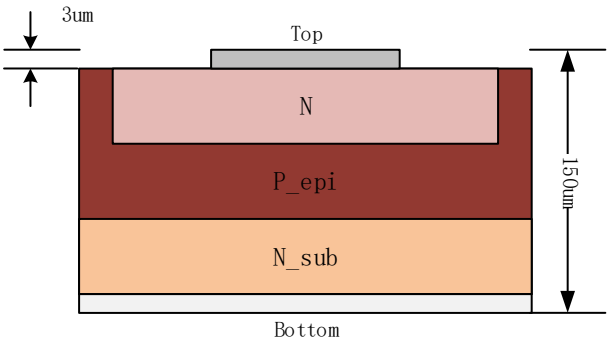
Structure

- Electrode topside：AlCu
- Electrode backside：Ag

Size

Parameter	Value（mil）	Value（mm）
Chip size	6.9mil x 6.9mil （±0.4mil）	0.175mm x 0.175mm（±0.01mm）
Chip Thickness	6mil ± 0.4mil	0.150mm ± 0.010mm
Top Metal Thickness	0.118mil	0.003mm
Pad Size	4.2mil±0.2mil	0.107mm±0.005mm





Electrical Characteristics(T= 25℃)

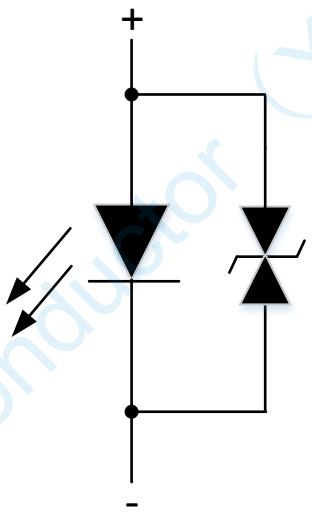
Parameter	Symbol	Test condition	Value	Unit
Junction temperature	Tj		150	℃
Storage temperature	Tstg		-55~150	℃

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Electrical Characteristics(T= 25℃)

Parameter	Symbol	Min	Type	Max	Unit	Test Conditions
Forward Voltage	V_F	5.8	-	8	V	I_F = 1mA
Forward Voltage	V_F	5.8	-	8	V	I_F = 10mA
Forward Leakage Current	I_F	-	-	50	nA	V_F = 5V
Reverse Voltage	V_R	5.8	-	8	V	I_R = 1mA
Reverse Voltage	V_R	5.8	-	8	V	I_R = 10mA
Reverse Leakage Current	I_R	-	-	50	nA	V_R = 5V
ESD	-	±30	-	-	kV	IEC 61000-4-2 (AIR)
ESD	-	±30	-	-	kV	IEC 61000-4-2 (CONTACT)

Schematic and PIN configuration



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